

SEMICONDUCTOR®

# FQP9N30

## N-Channel QFET<sup>®</sup> MOSFET 300 V, 9.0 A, 450 mΩ

### Description

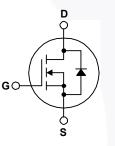
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

GDS

### Features

- + 9.0 A, 300 V,  $R_{DS(on)}$  = 450 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_{D}$  = 4.5 A
- Low Gate Charge (Typ. 17 nC)
- Low Crss (Typ. 16 pF)
- 100% Avalanche Tested





### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP9N30	Unit
V <sub>DSS</sub>	Drain-Source Voltage		300	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°	C)	9.0	A
	- Continuous (T <sub>C</sub> = 100	)°C)	5.7	A
DM	Drain Current - Pulsed	(Note 1)	36	A
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	420	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	9.0	A
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	9.8	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		98	W
	- Derate above 25°C		0.78	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Ran	nge	-55 to +150	°C
TL	Maximum Lead Temperature for Solderir 1/8" from Case for 5 seconds	ng,	300	°C

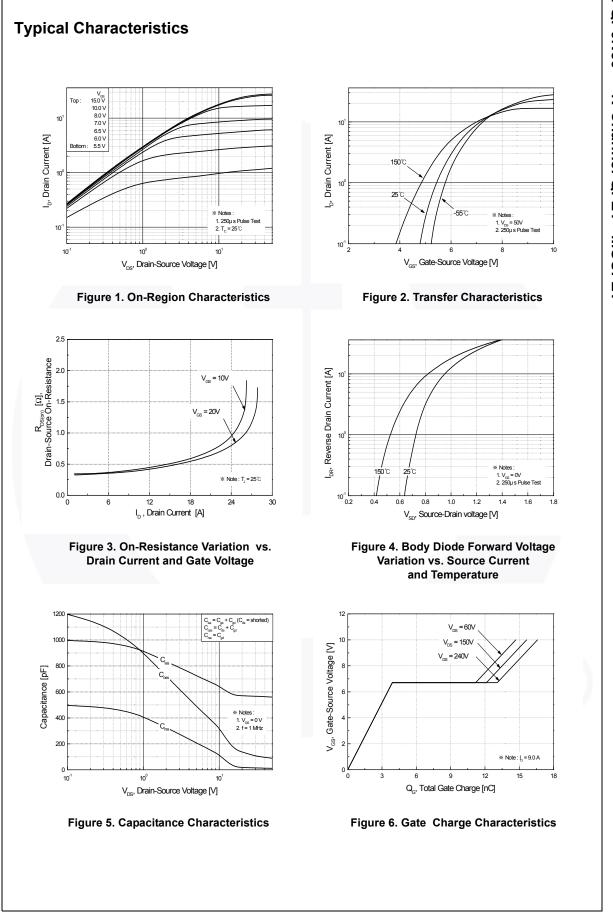
## **Thermal Characteristics**

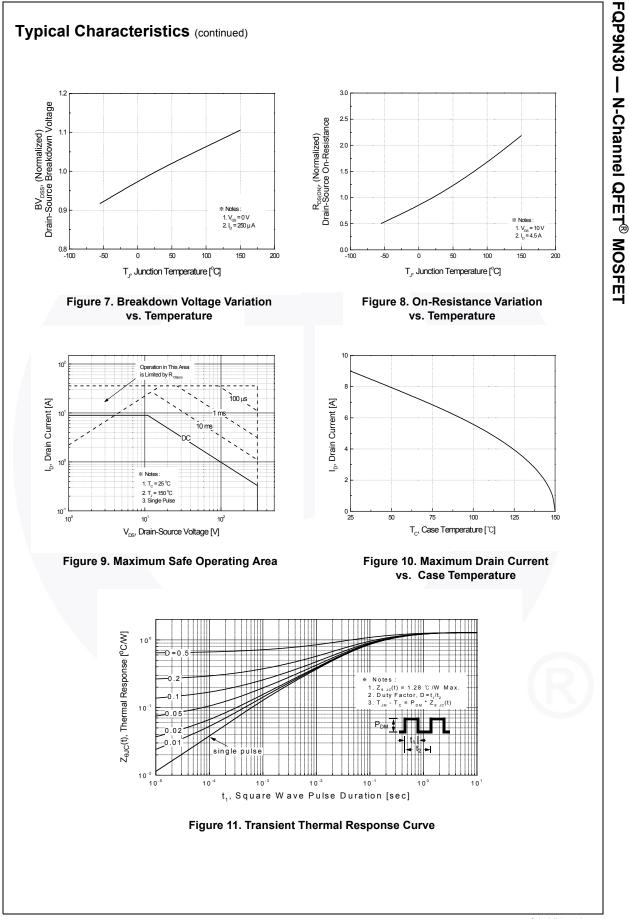
Symbol	Parameter	FQP9N30	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	1.28	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

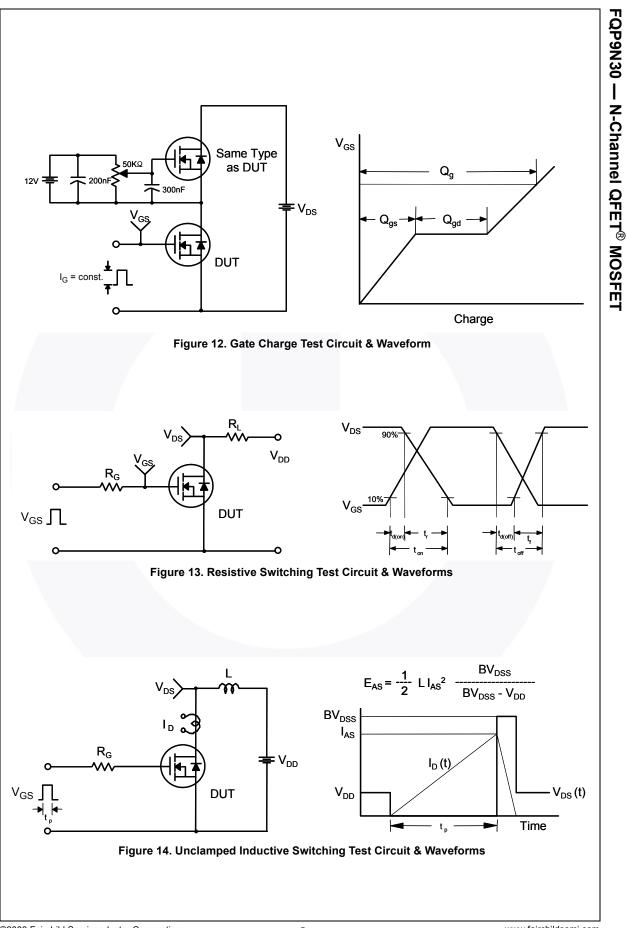
November 2013

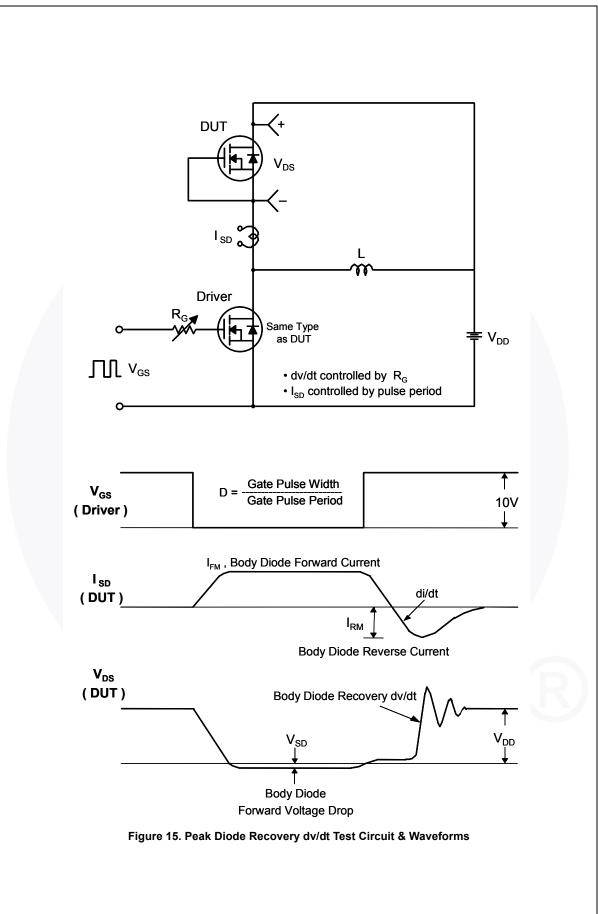
Part NumberTop MarkPackageFQP9N30FQP9N30TO-220		Package	Packing Method	Reel Size	Tape Width		th Q	Quantity	
		Tube N/A		N/A		5	50 units		
lectri	cal C	haracteristics	T <sub>C</sub> = 25°C	unless otherwise noted.					
Symbol		Parameter		Test Condit	ions	Min	Тур	Max	Unit
Off Cha	aracto	rietice							
BV <sub>DSS</sub>	1	Source Breakdown V	oltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 µ	ιA	300			V
ABV <sub>DSS</sub>	Breakdown Voltage Temperature Coefficient		$I_D = 250 \ \mu$ A, Referenced to 25°C					-	
$\Delta T_J$						0.28		V/°C	
DSS	Zero Gate Voltage Drain Current			$V_{DS}$ = 300 V, $V_{GS}$ = 0	) V			1	μA
			V <sub>DS</sub> = 240 V, T <sub>C</sub> = 125°C				10	μA	
GSSF	Gate-	Body Leakage Currer	t, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V				100	nA
GSSR	Gate-Body Leakage Current, Reverse		it, Reverse	$V_{GS}$ = -30 V, $V_{DS}$ = 0 V				-100	nA
On Cha	ractor	istics							
V <sub>GS(th)</sub>		Threshold Voltage		V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250	uА	3.0		5.0	V
R <sub>DS(on)</sub>		Drain-Source		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 4.5$			0.35	0.45	-
	On-Re	esistance					0.55	0.45	Ω
ØFS	Forwa	rd Transconductance		$V_{\rm DS}$ = 50 V, $I_{\rm D}$ = 4.5	A		4.9		S
Dvnam	ic Cha	racteristics							
C <sub>iss</sub>	Input Capacitance						570	740	pF
C <sub>oss</sub>	· · ·	t Capacitance		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz			120	155	pF
Crss	· · ·	se Transfer Capacita	nce				16	20	pF
Switch	ing Ch	aracteristics						1	
d(on)	Turn-C	On Delay Time		V <sub>DD</sub> = 150 V, I <sub>D</sub> = 9.0 A,			16	40	ns
r	Turn-C	On Rise Time		$R_G = 25 \Omega$	,		120	250	ns
d(off)	Turn-C	Off Delay Time		0			27	65	ns
f	Turn-C	Off Fall Time			(Note 4)		48	110	ns
ζ <sup>g</sup>	Total C	Sate Charge		V <sub>DS</sub> = 240 V, I <sub>D</sub> = 9.0	) A,		17	22	nC
2 <sub>gs</sub>	Gate-S	Source Charge		$V_{GS} = 10 V$ (Note 4)			3.9		nC
2 <sub>gd</sub>	Gate-I	Drain Charge					9.2		nC
				d Maximum Rati	ngs			0.0	۸
S		um Continuous Drain						9.0	A
SM		ium Pulsed Drain-So	1					36	A
/ <sub>SD</sub>		Source Diode Forwar	u voitage	$V_{GS} = 0 \text{ V, } I_S = 9.0 \text{ A}$ $V_{GS} = 0 \text{ V, } I_S = 9.0 \text{ A,}$ $dI_F / dt = 100 \text{ A}/\mu\text{s}$				1.5	V
m C		se Recovery Time					170		ns
ל <sup>ער</sup>	Reven	se Recovery Charge					1.4		μC

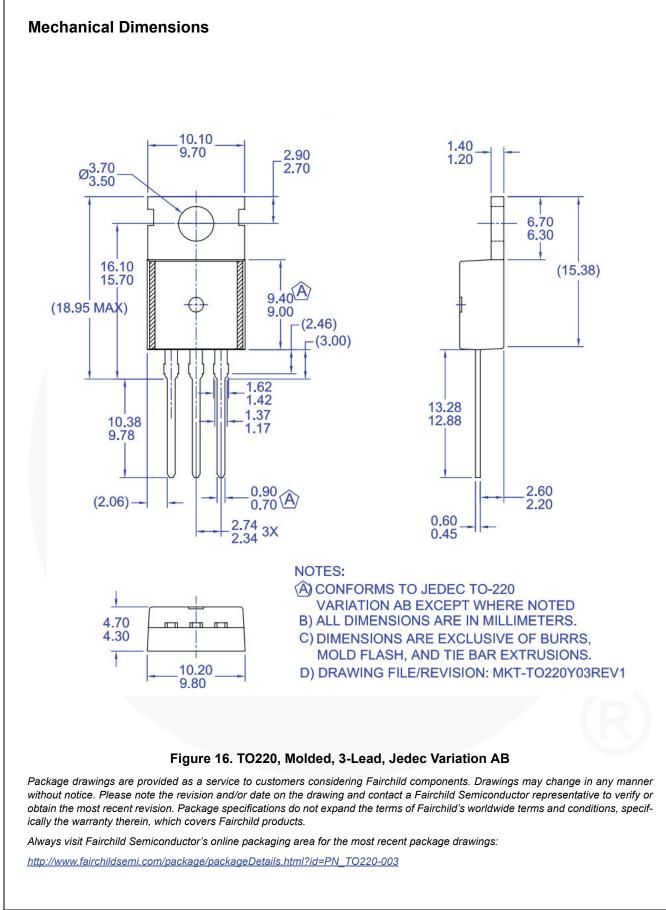
FQP9N30 — N-Channel QFET<sup>®</sup> MOSFET













SEMICONDUCTOR

### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™	F-PFS™
AX-CAP <sup>®</sup> *	FRFET®
BitSiC™	Global Power Resource <sup>SM</sup>
Build it Now™	GreenBridge™
CorePLUS™	Green FPS™
CorePOWER™	Green FPS™ e-Series™
CROSSVOLT™	G <i>max</i> ™
CTL™	GTO™
Current Transfer Logic™	IntelliMAX™
DEUXPEED®	ISOPLANAR™
Dual Cool™	Marking Small Speakers S
EcoSPARK <sup>®</sup>	and Better™
EfficentMax™	MegaBuck™
ESBC™	MICROCOUPLER™
R	MicroFET™
<b>F</b>	MicroPak™
Fairchild®	MicroPak2™
Fairchild Semiconductor <sup>®</sup>	MillerDrive™
FACT Quiet Series™	MotionMax™
FACT®	mWSaver®
FAST®	OptoHiT™

 $(1)_{\mathbb{B}}$ PowerTrench® PowerXS™ Programmable Active Droop™ QFET QS™ Quiet Series™ RapidConfigure™ rs Sound Louder Saving our world, 1mW/W/kW at a time™ SignalWise™ SmartMax™ SMART START™ Solutions for Your Success™ SPM<sup>®</sup> STEALTH™ SuperFET<sup>®</sup> SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS®

Sync-Lock™ SYSTEM<sup>®\*</sup> GENERAL TinyBoost TinyBuck® TinyCalc™ TinyLogic® TINYOPTO™ TinvPower™ TinyPWM™ TinyWire™ TranSiC™ TriFault Detect™ TRUECURRENT®\* uSerDes™ UHC® Ultra FRFET™ UniFFT™ VCX™ VisualMax™

VoltagePlus™

XS™

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

**OPTOLOGIC®** 

**OPTOPLANAR<sup>®</sup>** 

### DISCLAIMER

FastvCore™

FETBench™

FPS™

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

SvncFET™

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

### PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition		
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.		



# Authorized Distribution Brand :



## Website :

Welcome to visit www.ameya360.com

# Contact Us :

➤ Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

- > Sales :
  - Direct +86 (21) 6401-6692
  - Email amall@ameya360.com
  - QQ 800077892
  - Skype ameyasales1 ameyasales2

## > Customer Service :

Email service@ameya360.com

# > Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com